

What Is Claimed Is:

1. A susceptor of an approximately round disk shape, having a concave wafer pocket on a front surface thereof for accommodating a wafer, comprising:
  - a gas supply channel passing through from a side surface or a rear surface of the susceptor to the wafer pocket; and
  - a gas discharge channel passing through from the wafer pocket to the side surface or the rear surface of the susceptor.
2. The susceptor according to claim 1, wherein
  - the gas supply channel has a shape adapted to supply a gas into the wafer pocket as the susceptor rotates; and
  - the gas discharge channel has a shape adapted to discharge the gas present in the wafer pocket as the susceptor rotates.
3. An epitaxial wafer production apparatus comprising:
  - a chamber having a gas supply vent and a gas discharge vent;
  - a susceptor of an approximately round disk shape, which is disposed inside the chamber and comprises a concave wafer pocket on the front surface thereof for accommodating a wafer, a gas supply channel passing through from a side surface or a rear surface to the wafer pocket, and a gas discharge channel passing through from the wafer pocket to the side surface or the rear surface;
  - support means for supporting the susceptor; and
  - heating means for heating the susceptor and the wafer inside the chamber.

4. The epitaxial wafer production apparatus according to claim 3, comprising a gas supply vent for supplying a carrier gas containing a raw material gas only above the susceptor located inside the chamber.

5. An epitaxial wafer production apparatus comprising:

a chamber;

a susceptor disposed inside the chamber and comprising a concave wafer pocket on a front surface thereof for accommodating a wafer;

support means for supporting the susceptor; and

heating means for heating the susceptor and the wafer inside the chamber, wherein the apparatus further comprises:

a gas supply vent for supplying a carrier gas containing a raw material gas to above the susceptor located inside the chamber; and

a heavy gas supply vent for supplying a gas which is heavier than the carrier gas to under the susceptor located inside the chamber.

6. A method for producing an epitaxial wafer, comprising the steps of

placing a wafer into a concave wafer pocket formed on a front surface of a susceptor disposed inside a chamber;

supplying a gas from under the susceptor into the wafer pocket;

discharging a gas present inside the wafer pocket from under the susceptor; and

heating the susceptor and the wafer inside the chamber.

7. A method for producing an epitaxial wafer, comprising the steps of:  
placing a wafer onto a susceptor disposed inside a chamber;  
supplying a carrier gas containing a raw material gas to above the susceptor inside the chamber and supplying a gas heavier than the carrier gas to under the susceptor; and  
heating the susceptor and the wafer inside the chamber.